

## WHAT IS CLAIMED IS:

1. An etchant for etching at least one of a titanium material and silicon oxide, comprising a mixed liquid of HCl, NH<sub>4</sub>F and H<sub>2</sub>O.
2. An etchant according to claim 1, having a NH<sub>4</sub>F/HCl molar ratio of less than one.
3. A method for fabricating a semiconductor device, comprising the step of:  
etching a titanium material layer formed on a silicon oxide layer using an etchant according to claim 2.
4. An etchant according to claim 1, having a NH<sub>4</sub>F/HCl molar ratio of more than one.
5. A method for fabricating a semiconductor device, comprising the step of:  
etching a silicon oxide layer formed on a titanium material layer using an etchant according to claim 4.
6. An etchant according to claim 1, having a NH<sub>4</sub>F/HCl molar ratio of substantially one.
7. A method for fabricating a semiconductor device, comprising the step of:  
etching a lamination including a titanium material layer and a silicon oxide layer using an etchant according to claim 6.